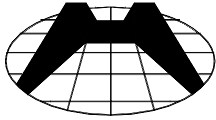
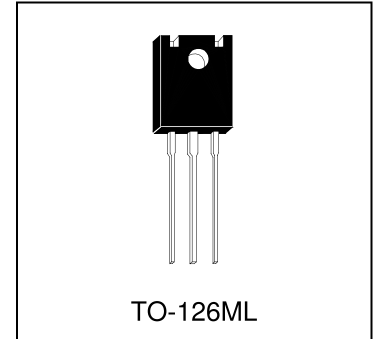


HI-SINCERITY
MICROELECTRONICS CORP.

Spec. No. : HE6630
Issued Date : 1995.12.18
Revised Date : 2006.07.27

HSD669A

NPN Epitaxial Planar Transistor



TO-126ML

Description

Low frequency power amplifier complementary pair with HSB649A

Absolute Maximum Ratings (T_A=25°C)

- Maximum Temperatures
  - Storage Temperature .... -55 ~ +150 °C
  - Junction Temperature .... +150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T_A=25°C) .... 1 W
  - Total Power Dissipation (T_C=25°C) .... 20 W
- Maximum Voltages and Currents
  - BV_{CBO} Collector to Base Voltage .... 180 V
  - BV_{CEO} Collector to Emitter Voltage .... 160 V
  - BV_{EBO} Emitter to Base Voltage .... 5 V
  - I_C Collector Current (DC) .... 1.5 A
  - I_C Collector Current (Pulse) .... 3 A

Electrical Characteristics (T_A=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	180	-	-	V	I_C=1mA, I_E=0
BV_{CEO}	160	-	-	V	I_C=10mA, I_B=0
BV_{EBO}	5	-	-	V	I_E=1mA, I_C=0
I_{CBO}	-	-	10	uA	V_{CB}=160V, I_E=0
*$V_{CE(sat)}$	-	-	1	V	I_C=500mA, I_B=50mA
$V_{BE(on)}$	-	-	1.5	V	I_C=150mA, V_{CE}=5V
*h_{FE1}	100	-	200		I_C=150mA, V_{CE}=5V
*h_{FE2}	30	-	-		I_C=500mA, V_{CE}=5V
f_T	-	140	-	MHz	I_C=150mA , V_{CE}=5V
Cob	-	14	-	pF	V_{CB}=10V, f=1MHz, I_E=0

*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

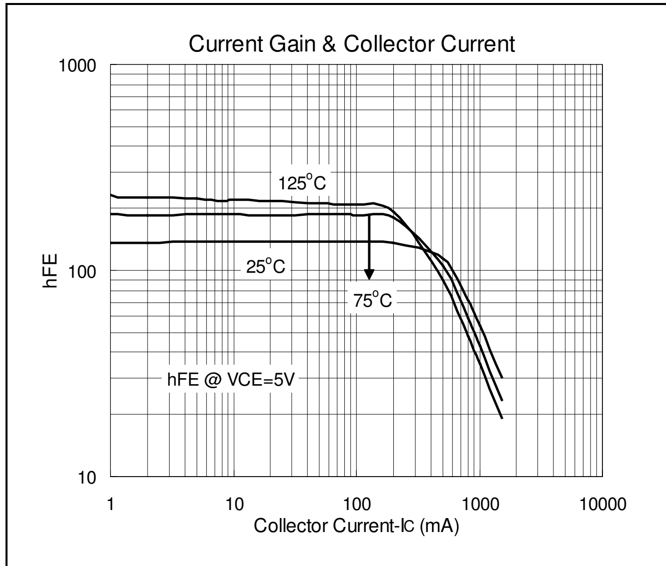
Thermal Characteristics

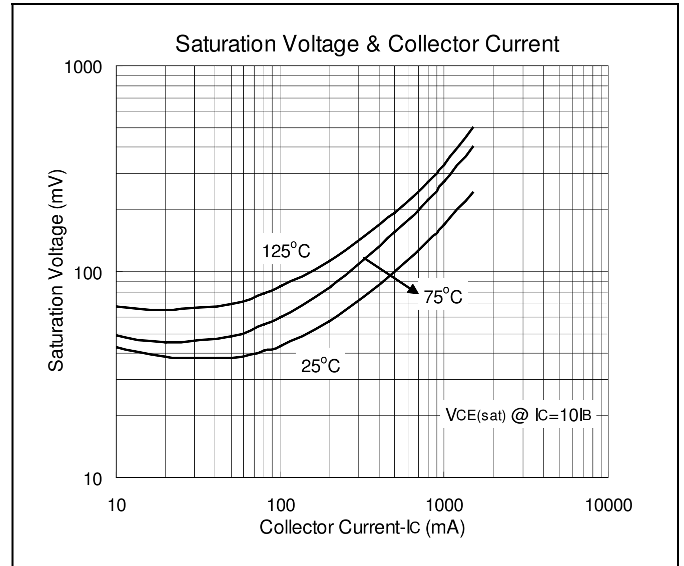
Symbol	Parameter	Value	Unit
R_{th-ja}	Thermal resistance from junction to ambient	125	^{O}C/W
R_{th-jc}	Thermal resistance from junction to case	6.25	^{O}C/W

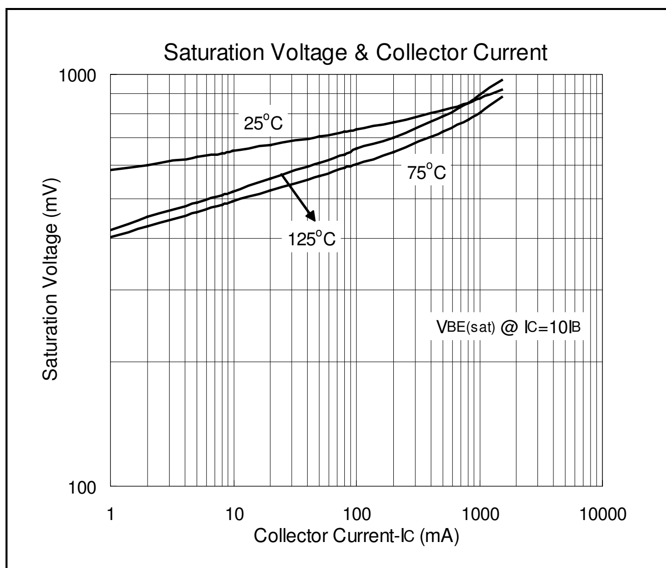
Classification Of h_{FE1}

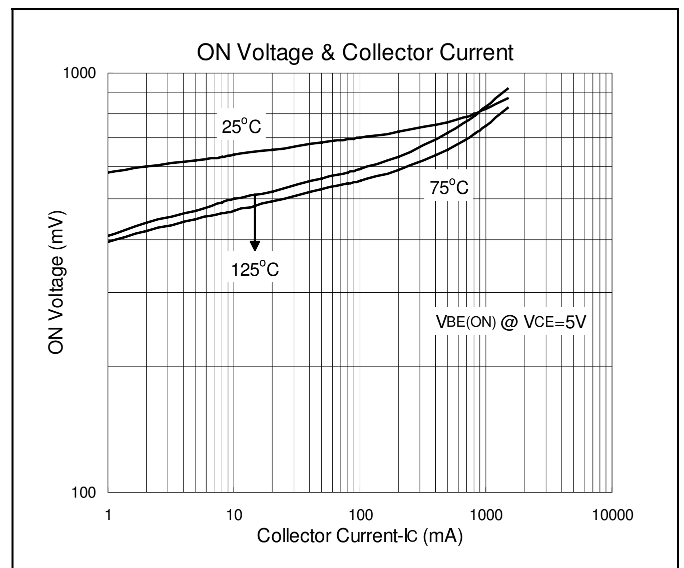
Rank	C
Range	100-200

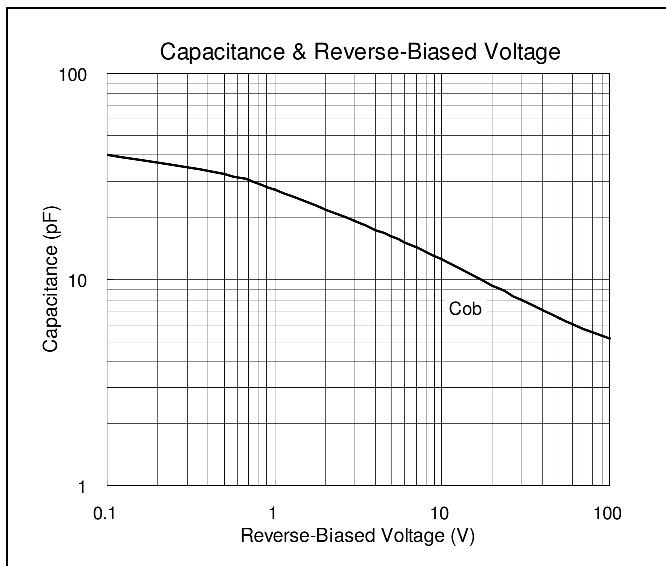
Characteristics Curve

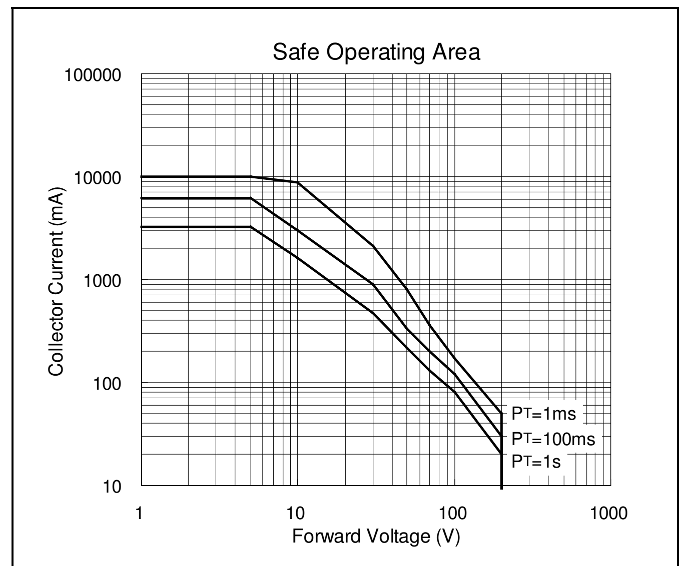












TO-126ML Dimension

Marking:

Note: Green label is used for pb-free packing

Pin Style: 1.Emitter 2.Collector 3.Base

Material:
- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	7.74	8.24
B	10.87	11.37
C	0.88	1.12
D	1.28	1.52
E	3.50	3.75
F	2.61	3.37
G	13	-
H	1.18	1.42
I	2.88	3.12
J	0.68	0.84
K	-	2.30
L	3.44	3.70
M	1.88	2.14
N	0.50	0.51

*: Typical, Unit: mm

3-Lead TO-126ML
Plastic Package
HSMC Package Code: D

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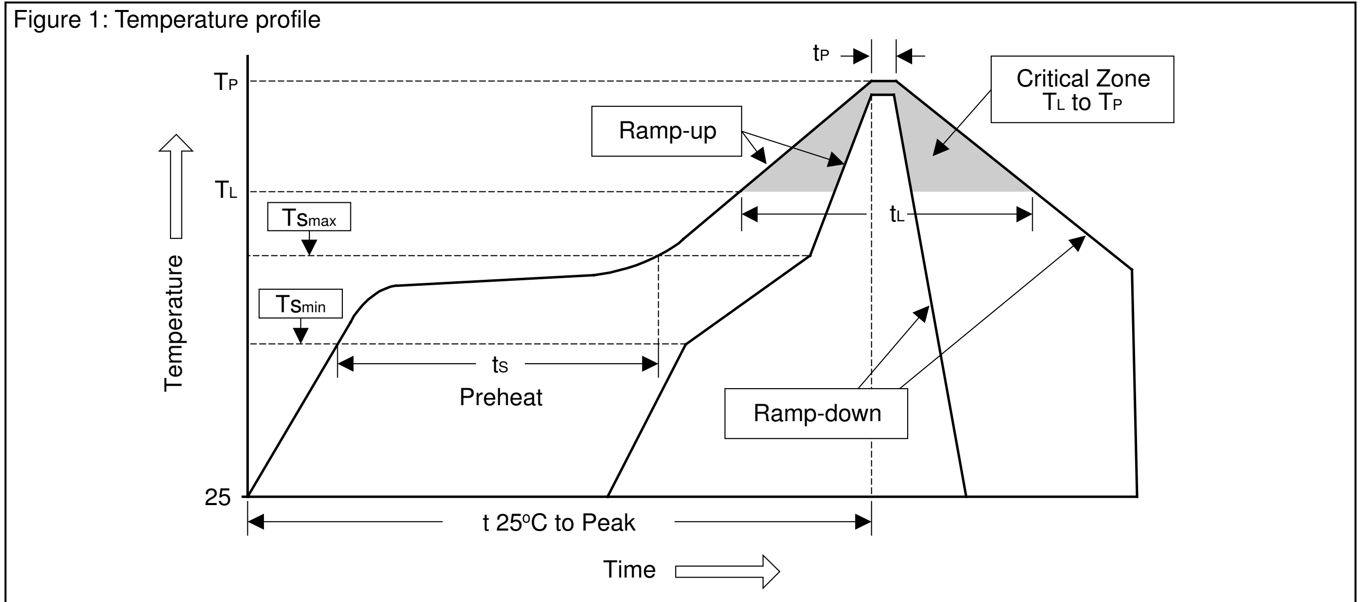
Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10ºC~35ºC Humidity=65%±15%

2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3ºC/sec	<3ºC/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100ºC 150ºC 60~120 sec	 150ºC 200ºC 60~180 sec
Tsmax to T_L - Ramp-up Rate	 <3ºC/sec	 <3ºC/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183ºC 60~150 sec	 217ºC 60~150 sec
Peak Temperature (T_P)	240ºC +0/-5ºC	260ºC +0/-5ºC
Time within 5ºC of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6ºC/sec	<6ºC/sec
Time 25ºC to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245ºC ±5ºC	10sec ±1sec
Pb-Free devices.	260ºC ±5ºC	10sec ±1sec